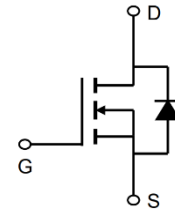


200V N-Channel Enhancement Mode MOSFET

Description

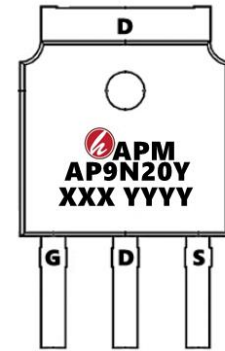
The AP9N20Y is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.



General Features

$V_{DS} = 200V$ $I_D = 9A$

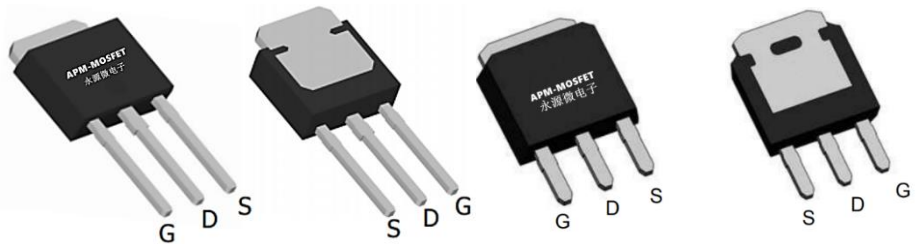
$R_{DS(ON)} < 300m\Omega$ @ $V_{GS}=10V$ (Type: 230m Ω)



Application

Uninterruptible Power Supply(UPS)

Power Factor Correction (PFC)



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP9N20Y	TO-251L-3L	AP9N20Y XXX YYYY	4000
AP9N20Y	TO-251S-3L	AP9N20Y XXX YYYY	4000

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
		TO-251	
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0V$)	200	V
I_D	Continuous Drain Current	9	A
I_{DM}	Pulsed Drain Current (note1)	36	A
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (note2)	100	mJ
I_{AR}	Avalanche Current (note1)	7.5	A
E_{AR}	Repetitive Avalanche Energy note1)	8.1	mJ
P_D	Power Dissipation ($T_C = 25^{\circ}C$)	74	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55~+150	$^{\circ}C$
R_{thJC}	Thermal Resistance, Junction-to-Case	1.7	$^{\circ}C/W$
R_{thJA}	Thermal Resistance, Junction-to-Ambient	62.5	$^{\circ}C/W$

200V N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	VGS = 0V, ID = 250μA	200	222	--	V
IDSS	Zero Gate Voltage Drain Current	VDS = 200V, VGS = 0V, T _J = 25°C	--	--	5	μA
IDSS	Zero Gate Voltage Drain Current	VDS = 160V, VGS = 0V, T _J = 125°C	--	--	100	
IGSS	Gate-Source Leakage	VGS = ±20V	--	--	±100	nA
VGS(th)	Gate-Source Threshold Voltage	VDS = VGS, ID = 250μA	2.0	3.5	4.0	V
RDS(on)	Drain-Source On-Resistance	VGS = 10V, ID = 4.5A	--	230	300	mΩ
Ciss	Input Capacitance	VGS = 0V, VDS = 25V, f = 1.0MHz	--	684	--	pF
Coss	Output Capacitance		--	103	--	
Crss	Reverse Transfer Capacitance		--	37	--	
Qg	Total Gate Charge	VDD = 160V, ID = 9.0A, VGS = 10V	--	23	--	nC
Qgs	Gate-Source Charge		--	2.5	--	
Qgd	Gate-Drain Charge		--	10	--	
td(on)	Turn-on Delay Time	VDD = 100V, ID = 9.0A, RG = 25 Ω	--	12	--	ns
tr	Turn-on Rise Time		--	22	--	
td(off)	Turn-off Delay Time		--	50	--	
tf	Turn-off Fall Time		--	48	--	
IS	Continuous Body Diode Current	TC = 25 °C	--	--	9	A
ISM	Pulsed Diode Forward Current		--	--	36	
VSD	Body Diode Voltage	T _J = 25°C, ISD = 9A, VGS = 0V	--	--	1.4	V
trr	Reverse Recovery Time	VGS = 0V, IS = 9A, diF/dt = 100A /μs	--	190	--	ns
Qrr	Reverse Recovery Charge		--	1.7	--	μC

Note :

- 1、 The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、 The EAS data shows Max. rating . IAS = 7.5A, VDD = 50V, RG = 25 Ω, Starting T_J = 25 °C
- 3、 The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

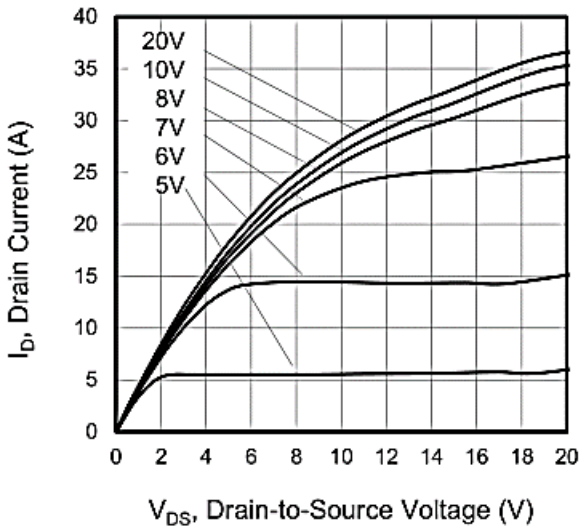


Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

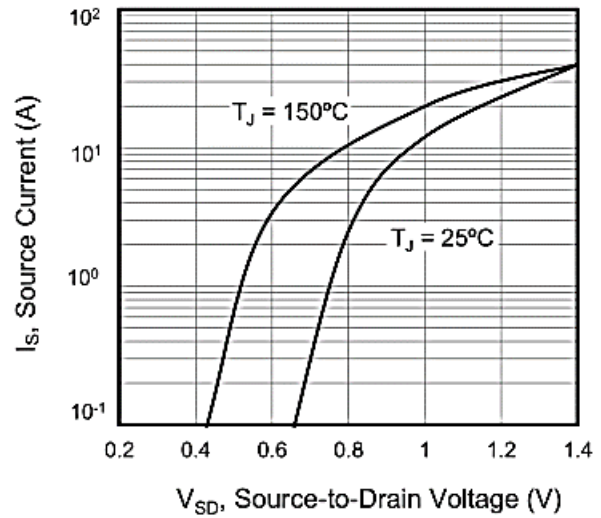


Figure 2. Body Diode Forward Voltage

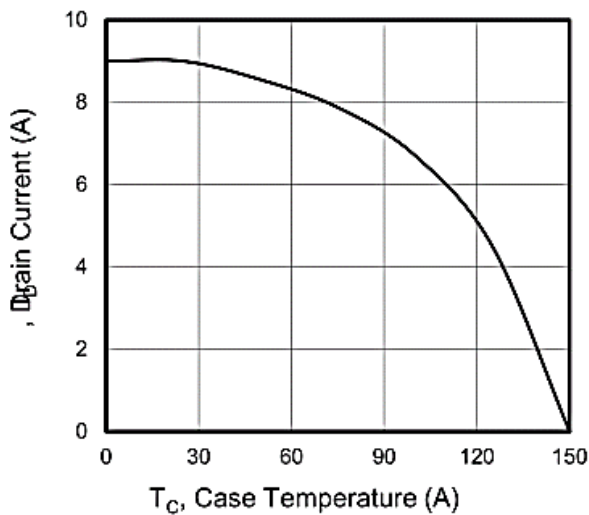


Figure 3. Drain Current vs. Temperature

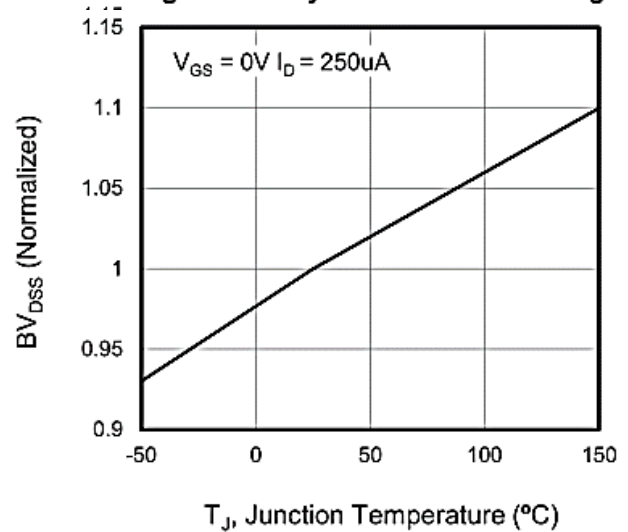


Figure 4. BV_{DSS} Variation vs. Temperature

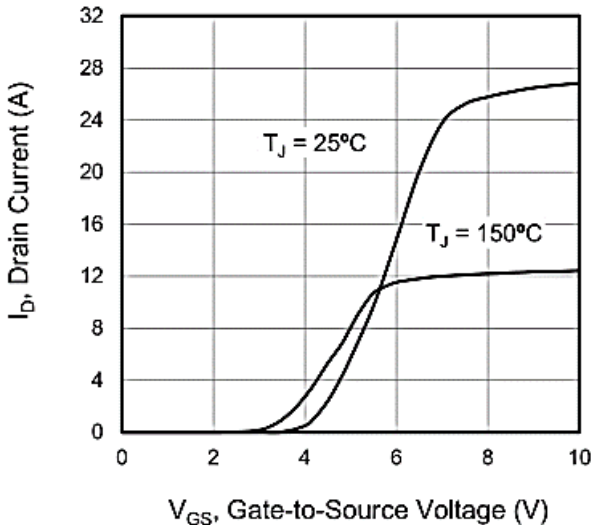


Figure 5. Transfer Characteristics

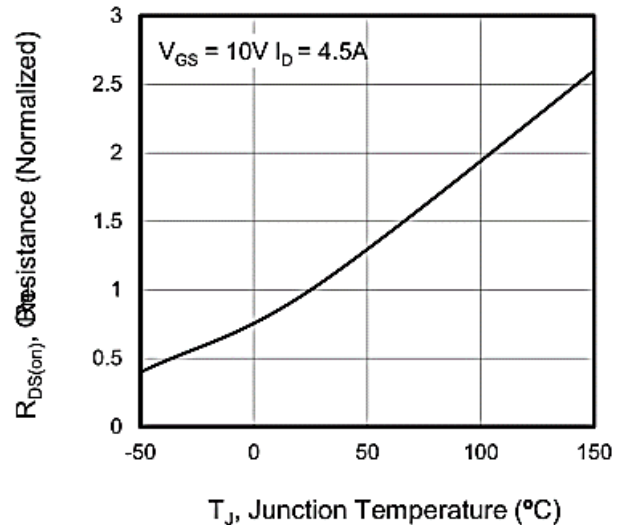


Figure 6. On-Resistance vs. Temperature



200V N-Channel Enhancement Mode MOSFET

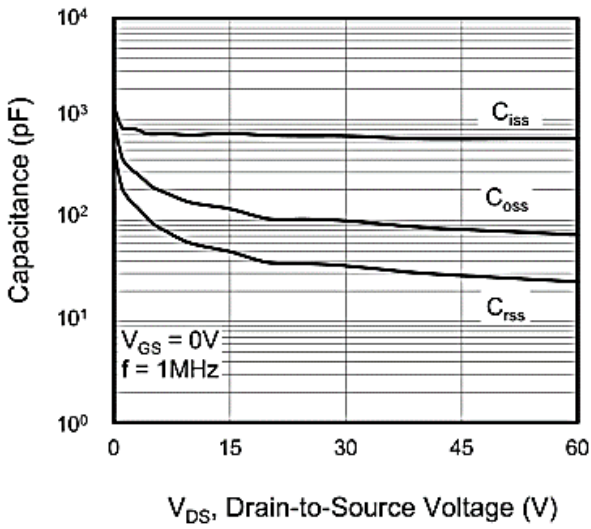


Figure 7. Capacitance

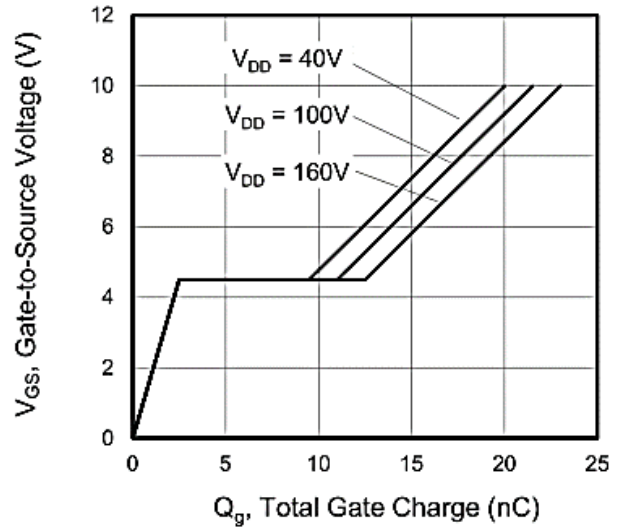


Figure 8. Gate Charge

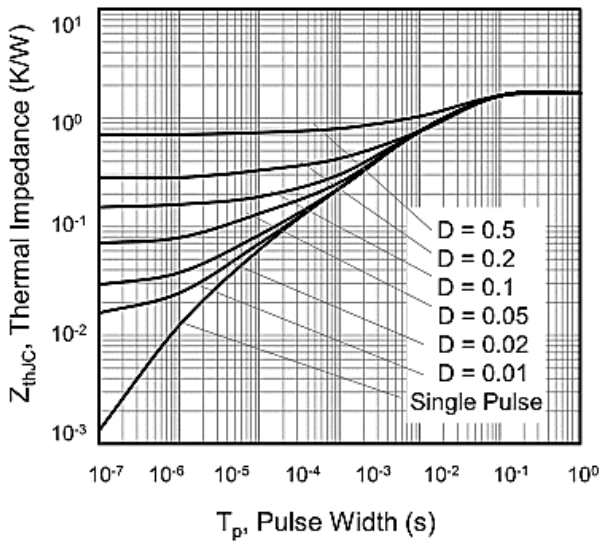
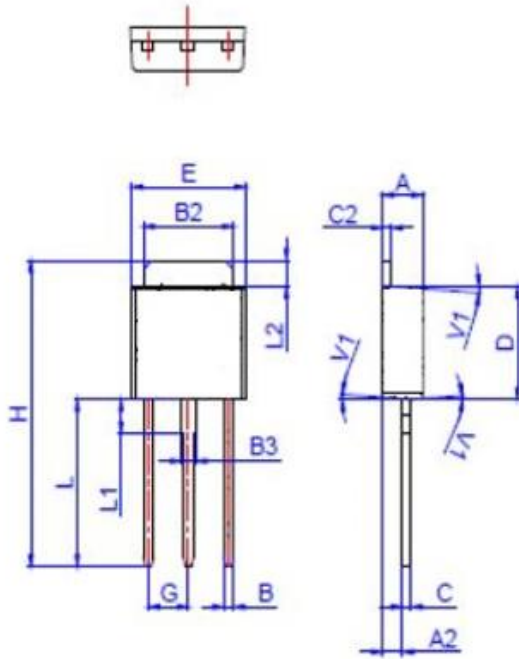


Figure 10. Transient Thermal Impedance

Package Mechanical Data-TO-251L-3L



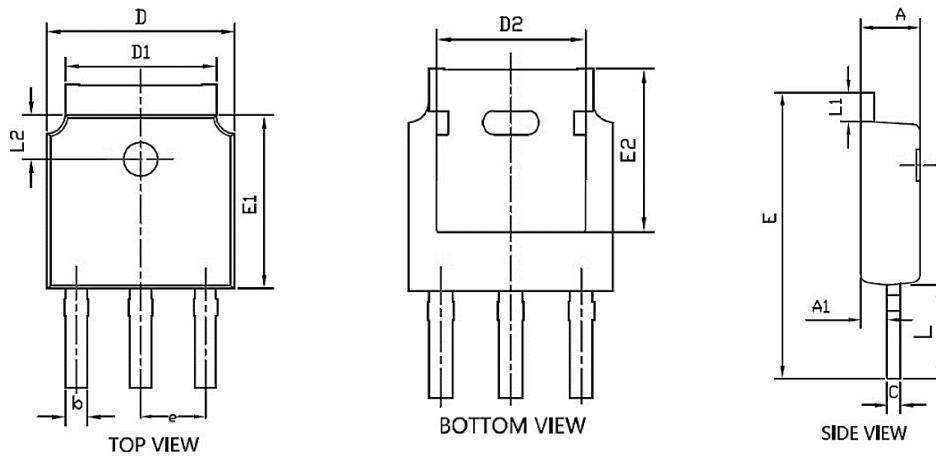
TO-251

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	

Package Information -TO-251

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	80	4,000	32,000

Package Mechanical Data-TO-251S-3L



Symbol	Common		
	mm		
	Mim	Nom	Max
A	2.2	2.3	2.4
A1	0.9	1.0	1.1
b	0.66	0.76	0.86
C	0.46	0.52	0.58
D	6.50	6.6	6.7
D1	5.15	5.3	5.45
D2	4.6	4.8	4.95
E	10.4	---	11.5
E1	6.0	6.1	6.2
E2	5.400REF		
e	2.286BSC		
L	3.5	4.0	4.3
L1	0.9	---	1.27
L2	1.4	---	1.9

200V N-Channel Enhancement Mode MOSFET**Attention**

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200V N-Channel Enhancement Mode MOSFET

Edition	Date	Change
Rve1.0	2021/1/31	Initial release

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